

Description

This 20V 8A N-Channel MOSFET in a DFN2×2-6L Plastic Package.

Features

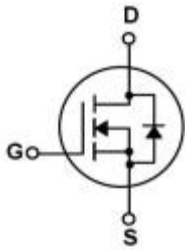
- V_{DS} (V) =20V
- $I_D = 8$ A ($V_{GS} = \pm 12$ V)
- Halogen-free Product

Applications

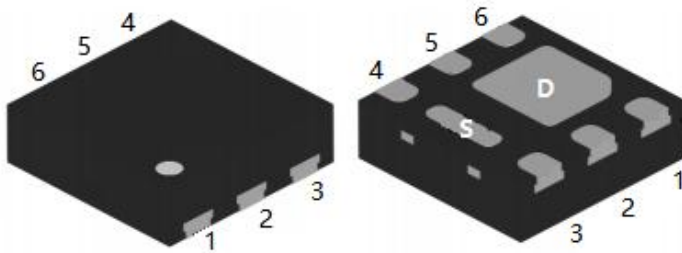
- Suited for low voltage applications such as automotive.
- DC/DC Converters.
- High efficiency switching for power management in portable and battery operated products.

V_{DSS}	$R_{DS(on)}$ (Typ)	I_D
20V	12.5m Ω	8A

Equivalent Circuit



Pinning



出脚	定义
Pin1	D
Pin2	D
Pin3	G
Pin4	S
Pin5	D
Pin6	D

Marking

See Marking Instructions

Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DSS}	20	V	
Drain Current	$I_D(T_C=25^\circ\text{C})$	8	A	
Gate-Source Voltage	V_{GS}	± 12	V	
Avalanche Current	I_{AS}	12	A	
Single Pulsed Avalanche Energy	E_{AS}	115	mJ	
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	2.8	W	
Junction Temperature Range	T_j	150	°C	
Storage Temperature Range	T_{stg}	-55~150	°C	
Maximum Junction-to-Ambient	t≤10s	$R_{\theta JA}$	45	°C/W
	Steady-State	$R_{\theta JA}$	80	

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	20	22		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V$ $V_{GS}=0V$			1.0	μA
		$V_{DS}=20V$ $T_J=150^\circ C$			50	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 12V$ $V_{DS}=0V$			± 0.1	μA
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=8.0A$		12.5	14	$m\Omega$
		$V_{GS}=4.5V$ $I_D=8.0A$		13.9	20	$m\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	0.4	0.8	1.2	V
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_F=1.0A$		0.7	1.2	V
Signal Source Resistance	R_g	$F=1MHz$		3.3		Ω
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		460		pF
Output Capacitance	C_{oss}			75		
Reverse Transfer Capacitance	C_{rss}			65		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=10V$ $V_{GS}=4.5V$ $R_L=1.25\Omega$ $R_{GEN}=3\Omega$		2.7		ns
Turn-On Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			37		
Turn-Off Fall Time	t_f			7		
Total Gate Charge	Q_g	$V_{DS}=10V$ $V_{GS}=4.5V$ $I_D=8A$		12.5		nC
Gate-Source Charge	Q_{gs}			1.2		
Gate-Drain Charge	Q_{gd}			2.7		

Electrical Characteristic Curve

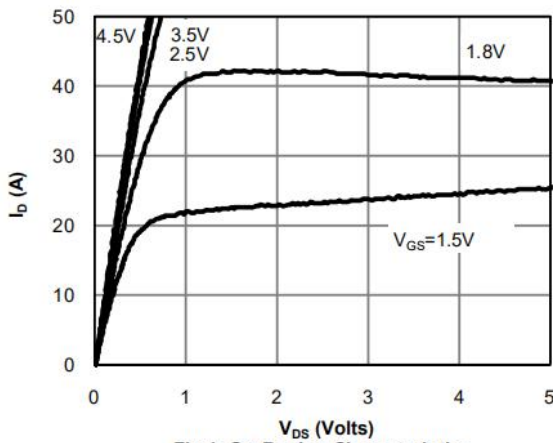


Fig 1: On-Region Characteristics

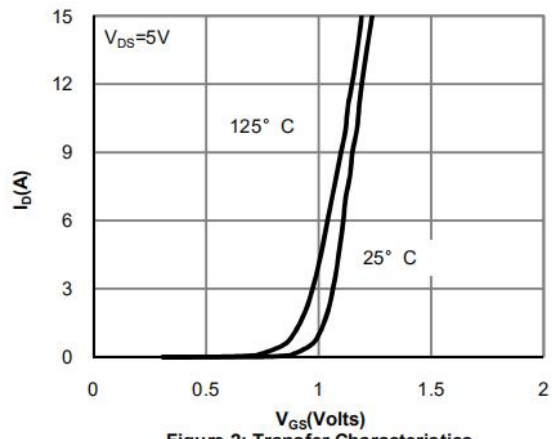


Figure 2: Transfer Characteristics

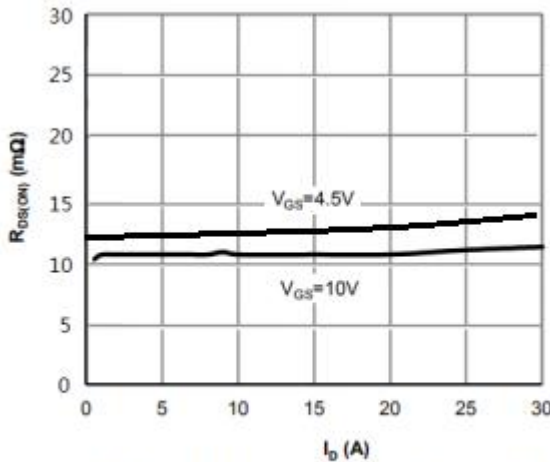


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

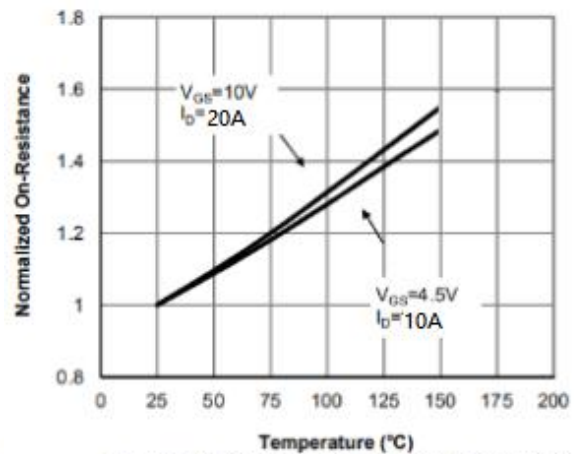


Figure 4: On-Resistance vs. Junction Temperature

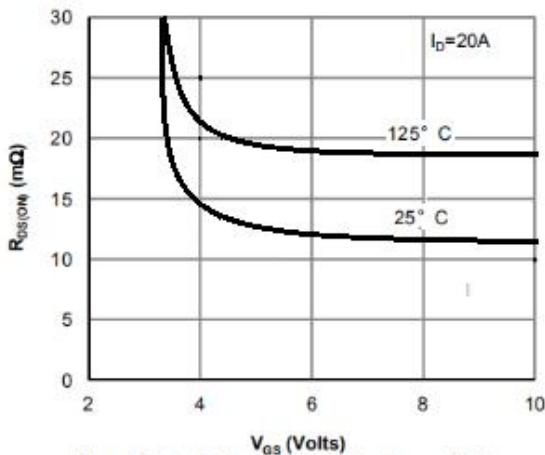


Figure 5: On-Resistance vs. Gate-Source Voltage

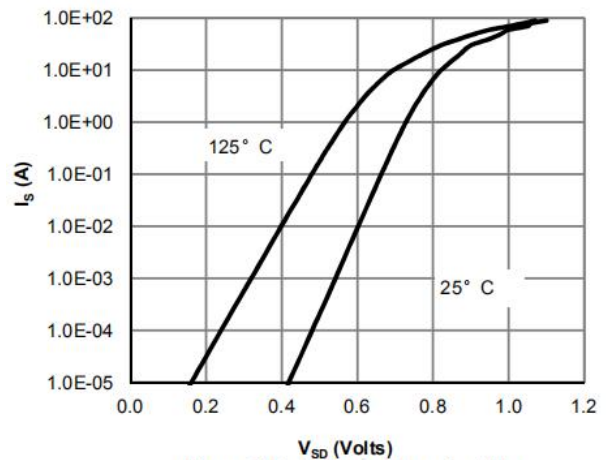


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

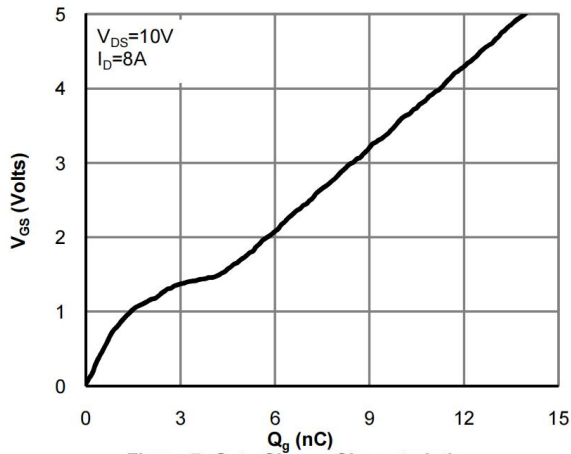


Figure 7: Gate-Charge Characteristics

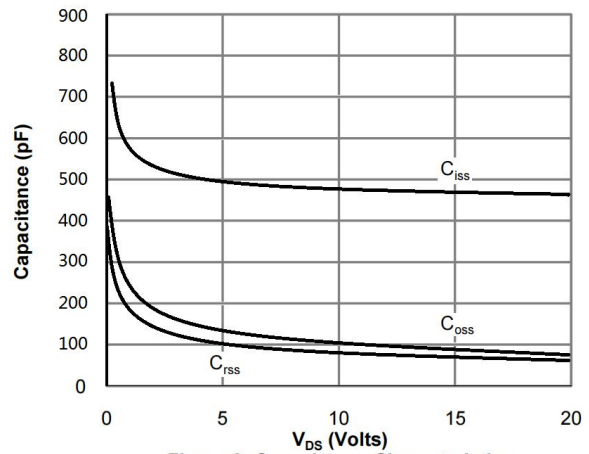


Figure 8: Capacitance Characteristics

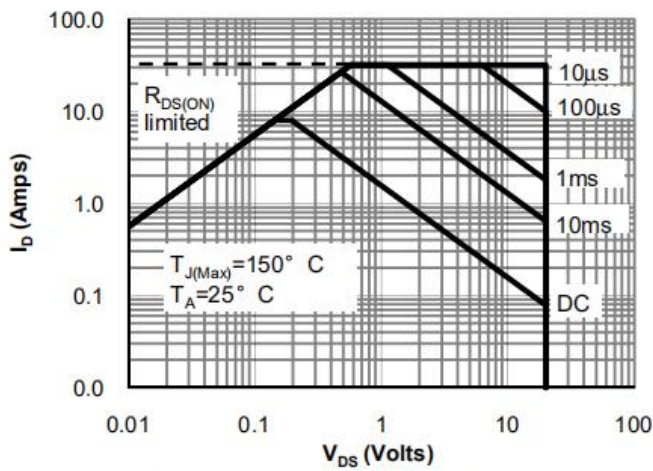


Figure 9: Maximum Forward Biased Safe Operating Area

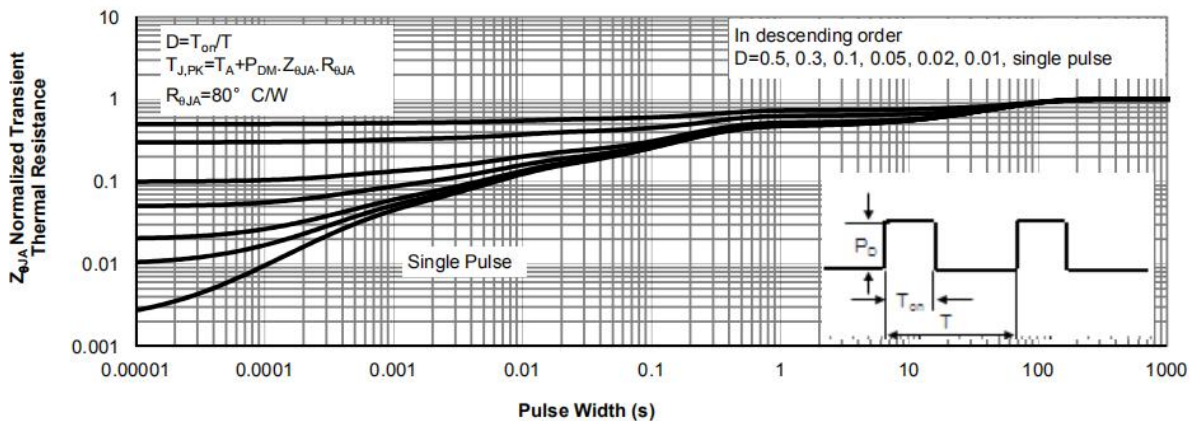


Figure 10: Normalized Maximum Transient Thermal Impedance

Marking Instructions



Note:

COT: Company Code.

120N02L: Product Type

****: Lot No. Code, code change with Lot No.

Packaging SPEC.

REEL INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
DFN2×2-6L	4,000	10	40,000	4	160,000	7" ×8	210×205×205	445×230×435

Package Outline Dimensions

DFN2x2-6L-0.5

Unit:mm

